IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Evgueniy Nikolov Stefanov et al

FILED: Concurrently Herewith

FOR: SYMMETRICAL HIGH FREQUENCY SCR

STRUCTURE & METHOD

Date: 7/7/2003

DISCLOSURE STATEMENT UNDER 37 C.F.R. 1.56

Honorable Assistant Commissioner for Patents Washington, D.C. 20231

SIR:

It is respectfully requested that the prior art listed on FORM PTO-1449 be considered in the examination of the subject application and made of record therein. A copy of the listed prior art is enclosed herewith.

No representation is made or intended that the listed prior art enclosed herewith is material to patentability of the subject patent application.

No representation is made or intended that a search has been made or that no better prior art than that listed is available.

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Respectfully submitted, Evgueniy Nikolov Stefanov et

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SERIAL NO. Form PTO-ATTY, DOCKET NO. 1449 LIST OF PATENTS AND PUBLICATIONS Ons00393 **FOR** APPLICANT'S INFORMATION APPLICANT DISCLOSURE **Evgueniy Nikolov Stefanov et** STATEMENT FILING DATE GROUP (Use Several Sheets if Necessary) CONCURRENTLY

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

Examiner Document Number Initial									Date	Name	Class	Sub- Class	Filing date (If approp riate)
AA		5	8	4	4	2	8	0	12/1/1998	Kim	H01L	23/62	
AB		6	3	2	3	0	7	4	11/27/2001	Jiang et al	H01L	28/8238	
AC		5	6	0	2	4	0	4	2/11/1997	Chen et al	H01C	31/111`	
AD		6	2	6	8	9	9	2	7/31/2001	Lee et al	H02H	3/22	
AE		5	9	5	9	8	2	1	9/28/1999	Voogel	H02H	3/22	
AF		5	7	4	2	0	8	5	4/21/1998	Yu	H01L	23/62	
AG		5	5	4	1	8	0	1	7/30/1996	Lee et al	H02H	9/04	
AH		5	4	5	2	1	7	1	9/19/1995	Metz et al	H01L	29/06	
Al		5	0	7	2	2	7	3	12/10/1991	Avery	H01L	29/72	
AJ		5	5	7	6	5	5	7	11/19/1996	Ker et al	H01L	29/74	
AK		5	5	7	2	3	9	4	11/5/1996	Ker et al	H02H	9/00	
AL	2002	0	1	5	4	4	6	3	10/24/2002	Mergens et al	H02H	9/00	
AM	2002	0	1	5	3	6	7	1	10/24/2002	Raymond et al	F16L	17/06	

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document #				Date		Country	 Class/subclass Tran			lation - No			
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

AS	5	IEEE Electron Device Letters, Vol 12, No. 1, January 1991, pages 21-22, Chatterjee et al., "A Low-Voltage Triggering SCR for On-Chip ESD Protection at Output and Input Pads"
АТ	-	IEEE Transactions on Electron Devices, Vol. 43, No. 4, April 1996, pages 588-598, Ker et al., "Complementary-LVTSCR ESD Protection Circuit for Submicron CMOS VLSI/ULSI"
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AV	,	
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EXAMINER

DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.